## MDD72-08N1B

## **Standard Rectifier Module**

$V_{RRM}$	<i>=</i> 2x	800 V
I <sub>fav</sub>	=	99 A
V <sub>F</sub>	=	1.22 V

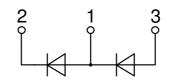
Phase leg

Part number MDD72-08N1B



Backside: isolated **E**72873

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### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- · Very low leakage current

### **Applications:**

- Diode for main rectification
- For single and three phase
- bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- · Field supply for DC motors

### Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

### Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

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# MDD72-08N1B

Rectifier					Rating	S	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse bloc	king voltage	$T_{VJ} = 25^{\circ}C$			900	V
V <sub>RRM</sub>	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			800	V
I <sub>R</sub>	reverse current	$V_{R} = 800 V$	$T_{VJ} = 25^{\circ}C$			200	μA
		$V_{R} = 800 V$	$T_{vJ} = 150^{\circ}C$			15	mA
VF	forward voltage drop	I <sub>F</sub> = 150 A	$T_{VJ} = 25^{\circ}C$			1.27	V
		I <sub>F</sub> = 300 A				1.60	V
		I <sub>F</sub> = 150 A	T <sub>VJ</sub> = 125 °C			1.22	V
		$I_{F} = 300 \text{ A}$				1.60	V
FAV	average forward current	T <sub>c</sub> = 100°C	$T_{vJ} = 150 ^{\circ}\text{C}$			99	Α
F(RMS)	RMS forward current	180° sine				180	Α
V <sub>F0</sub>	threshold voltage $T_{yJ} = 150^{\circ}C$					0.80	V
r <sub>F</sub>	slope resistance } for power	loss calculation only				2.3	mΩ
R <sub>thJC</sub>	thermal resistance junction to ca	ase				0.35	K/W
R <sub>thCH</sub>	thermal resistance case to heats	sink			0.20		K/W
P <sub>tot</sub>	total power dissipation		$T_c = 25^{\circ}C$			357	W
I <sub>FSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			1.70	kA
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			1.84	kA
		t = 10 ms; (50 Hz), sine	T <sub>vj</sub> = 150°C			1.45	kA
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			1.56	kA
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			14.5	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			14.0	kA²s
		t = 10 ms; (50 Hz), sine	$T_{vJ} = 150$ °C			10.4	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			10.1	kA²s
C	junction capacitance	V <sub>B</sub> = 400 V; f = 1 MHz	$T_{VJ} = 25^{\circ}C$		116		pF

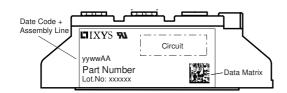
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# MDD72-08N1B

Package	TO-240AA				F	Ratings	S	
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal					200	Α
T <sub>vj</sub>	virtual junction temperature				-40		150	°C
T <sub>op</sub>	operation temperature				-40		125	°C
T <sub>stg</sub>	storage temperature				-40		125	°C
Weight						76		g
M <sub>D</sub>	mounting torque				2.5		4	Nm
M <sub>T</sub>	terminal torque				2.5		4	Nm
<b>d</b> <sub>Spp/App</sub>	creenage distance on surfac	e   striking distance through air	terminal to terminal	13.0	9.7			mm
<b>d</b> <sub>Spb/Apb</sub>	creepage distance on surrac	e   sunking uistance through an	terminal to backside	16.0	16.0			mm
	isolation voltage	t = 1 second			3600			V
		t = 1 minute	50/60 Hz, RMS; liso∟ ≤ 1 mA		3000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD72-08N1B	MDD72-08N1B	Box	36	453137

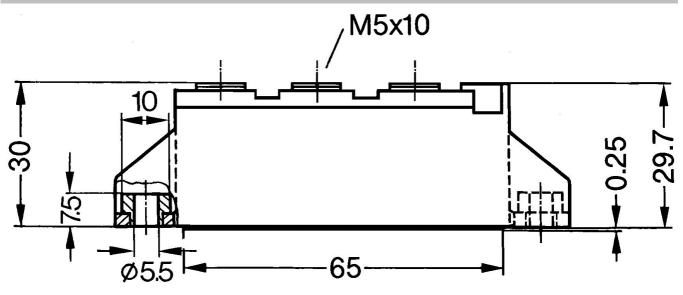
Similar Part	Package	Voltage class
MDD72-12N1B	TO-240AA	1200
MDD72-14N1B	TO-240AA	1400
MDD72-16N1B	TO-240AA	1600
MDD72-18N1B	TO-240AA	1800

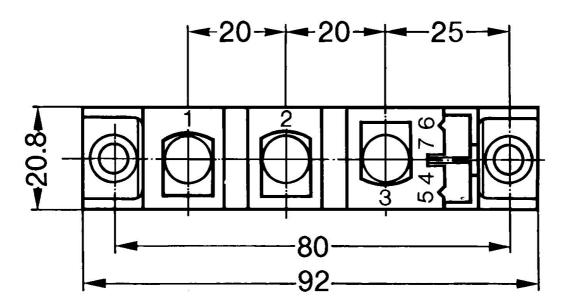
Equivalent Circuits for Simulation			* on die level	T <sub>vj</sub> = 150 °C
	$-R_{o}$	Rectifier		
$V_{0 \text{ max}}$	threshold voltage	0.8		V
$\mathbf{R}_{0 \max}$	slope resistance *	1.1		mΩ

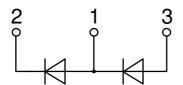
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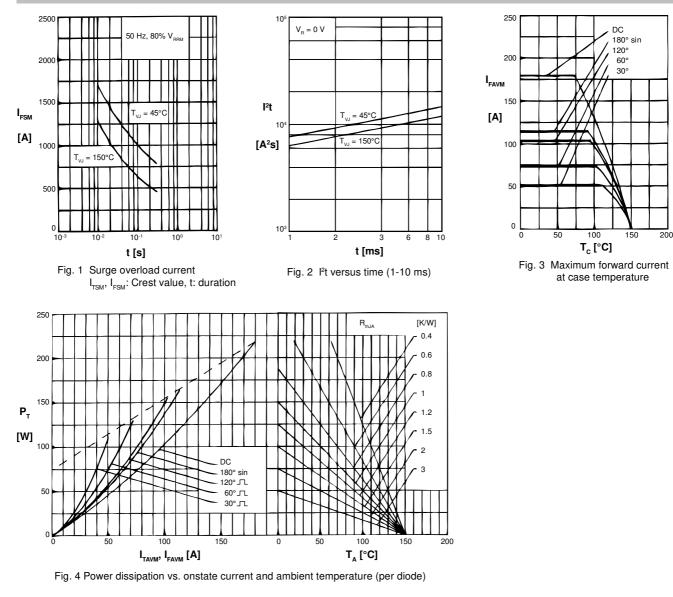
Outlines TO-240AA







### Rectifier



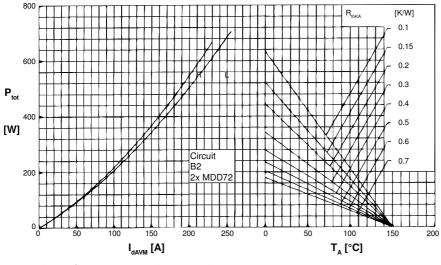


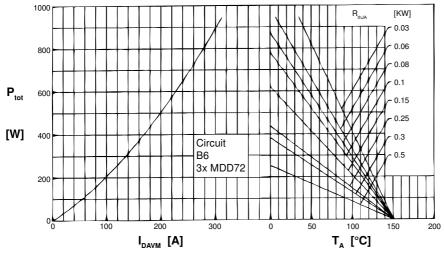
Fig. 6 Single phase rectifier bridge: Power dissipation versus direct output current and ambient temperature; R = resistive load, L = inductive load

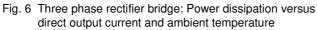
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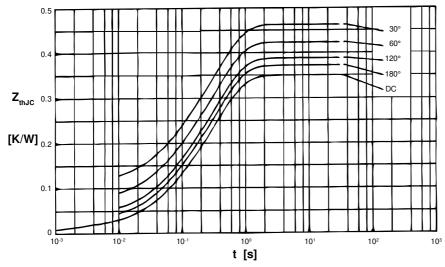
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## MDD72-08N1B

### Rectifier





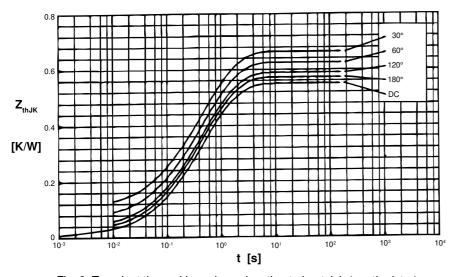


	d	R <sub>thJC</sub> [	K/W]		
	DC	0.3	5		
	180°	0.3	7		
	120°	0.3	9		
	60°	0.4	3		
	30°	0.4	7		
Constants for $Z_{thJC}$ calculation:					
i	R <sub>thi</sub> [K	[/W]	t <sub>i</sub> [s]		
1	0.01	3	0.0014		
0	0.07	70	0 0620		

 ${\rm R}_{\rm thJC}$  for various conduction angles d:

1	0.013	0.0014
2	0.072	0.0620
3	0.265	0.3750

Fig. 7 Transient thermal impedance junction to case (per diode)



${\rm R}_{_{thJK}}$ for various conduction angles d:			
	d R <sub>tt</sub>	<sub>JK</sub> [K/W]	
	DC	0.55	
	180°	0.57	
	120°	0.59	
	60°	0.63	
	30°	0.67	
Co i 1	R <sub>thi</sub> [K/W	r Z <sub>thJK</sub> calculation: ] <b>t<sub>i</sub> [s]</b> 0.0014	
2	0.072	0.0620	
3	0.265	0.3750	
4	0.200	1.3200	

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Fig. 8 Transient thermal impedance junction to heatsink (per thyristor)

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